



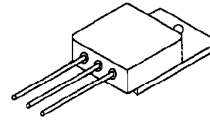
NES
NEW ENGLAND SEMICONDUCTOR

NESY230

POWER MOSFET N CHANNEL

- REPETITIVE AVALANCHE RATINGS
- LOW $R_{DS(ON)}$
- LOW DRIVE REQUIREMENT
- DYNAMIC dv/dt RATING

TO-257AA



6 AMPERE

200 VOLTS

0.40 Ω

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

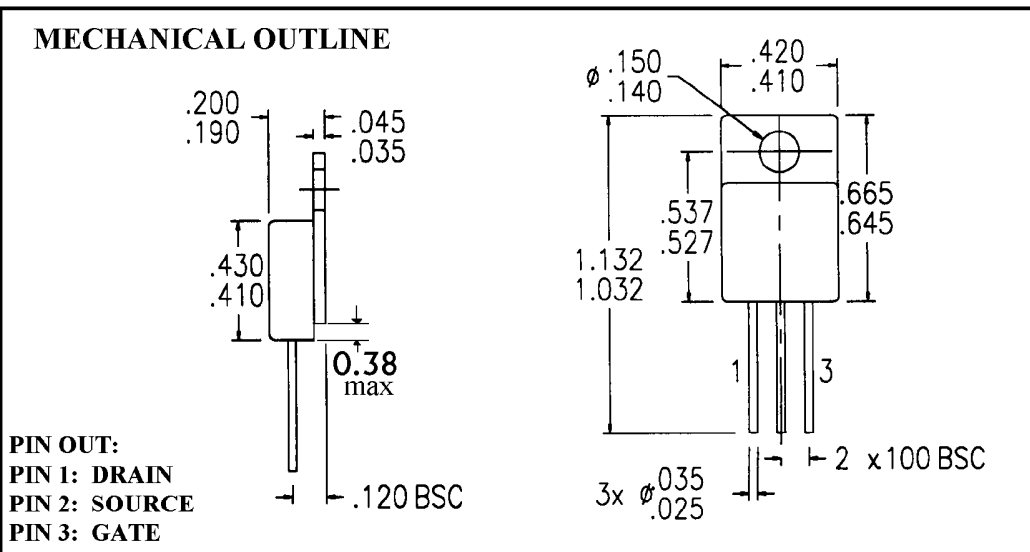
PARAMETERS / TEST CONDITIONS	SYMBOL	VALUE	UNITS
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	6.0	A
Pulsed Drain Current (1)	I_{DM}	24	A
Power Dissipation	P_D	50 38	W
Operating Junction & Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Lead Temperature (1/16" from case for 10 secs.)	T_L	300	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYP.	MAX.	UNITS
Junction-to-Case	R_{thJC}		2.5	K/W

(1) Pulse width limited by maximum junction temperature.

MECHANICAL OUTLINE



NEW ENGLAND SEMICONDUCTOR

6 Lake Street Lawrence, MA 01841
 1-800-446-1158 / (978) 794-1666 / FAX: (978) 689-0803

T4-4.8-860-926 REV: --



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NESY230

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

PARAMETERS / TEST CONDITIONS		SYMBOL	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$		$V_{(BR)DSS}$	200			V
Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$		$V_{GS(th)}$	2.0		4.0	V
Gate-Body Leakage $V_{GS} = \text{At Rated } V_{GS}$		I_{GSS}			± 100	nA
Zero Gate Voltage Drain Current $V_{DS} = 0.8\ \text{max Rating}, V_{GS} = 0\text{ V}$		I_{DSS}			250	μA
Zero Gate Voltage Drain Current $V_{DS} = 80\% V_{(BR)DSS}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$		I_{DSS}			1000	μA
Drain-Source On-State Resistance (2) $V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		$r_{DS(on)}$			0.4	Ω
Forward Transconductance (2) $V_{DS} = 15\text{ V}, I_D = 5\text{ A} (V_{DS} \geq I_{D(ON)} \times R_{DS(ON)} \text{ max})$		g_{fs}	3.0			S(Ω)
Input Capacitance	$V_{GS} = 0\text{ V}$	C_{iss}			800	pF
Output Capacitance	$V_{DS} = 25\text{ V}$	C_{oss}			450	
Reverse Transfer Capacitance	$f = 1\text{ MHz}$	C_{rss}			150	
Total Gate Charge	$V_{DS} = 80\% V_{(BR)DSS}$ $V_{GS} = 10\text{ V}, I_D = 12\text{ A}$ (Gate charge is essentially independent of operating temperature.)	Q_g			30	nC
Gate-Source Charge		Q_{gs}				
Gate -Drain Charge		Q_{gd}				
Turn-On Delay Time	$V_{dd} = 50\% V_{DS},$ $I_D = 50\% A,$ $R_G = 15\ \Omega$ (Switching time is essentially independent of operating temperature.)	$t_{d(on)}$			30	ns
Rise Time		t_r			50	
Turn-Off Delay Time		$t_{d(off)}$			50	
Fall Time		t_f			40	

SOURCE-DRAIN DIODE RATINGS & CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

PARAMETERS / TEST CONDITIONS		SYMBOL	MIN.	TYP.	MAX.	UNITS
Continuous Current		I_S			6.0	A
Pulsed Current (1)		I_{SM}			24	A
Forward Voltage (2) $I_F = I_S, V_{GS} = 0\text{ V}$		V_{SD}			2.0	V
Reverse Recovery Time $I_F = I_S, di/dt = 100\text{ A}/\mu\text{S}, V_{DD} = 50\text{ V}$		t_{rr}			450	ns
Reverse Recovered Charge $I_F = I_S, di/dt = 100\text{ A}/\mu\text{S}, V_{DD} = 50\text{ V}$		Q_{rr}			6.0	μC

(1) Pulsed width limited by maximum junction temperature.

(2) Pulse Test: Pulse width < 300 μsec . Duty cycle $\leq 2\%$.

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